

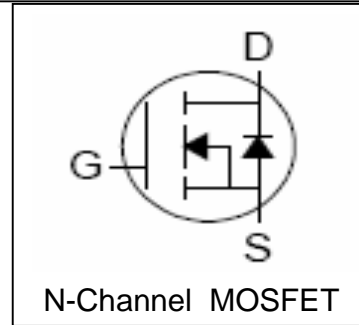
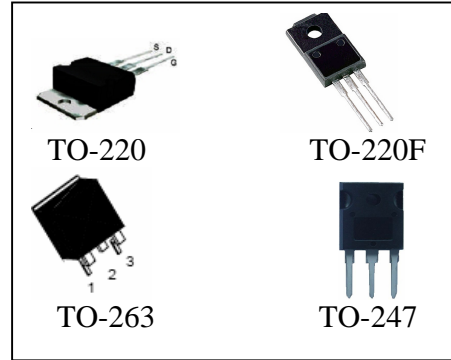
Features

- 40V/220A
 $R_{DS(ON)}=2.3\text{ m}\Omega(\text{Typ.}) @ V_{GS}=10\text{V}$
- Avalanche Rated
- Reliable and Rugged
- Lead Free and Green Devices Available

Applications

- Automotive applications and a wide variety of other applications
- High Efficiency Synchronous in SMPS
- High Speed Power Switching

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	40	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 220 ^②	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulsed Drain Current Tested	$T_C=25^\circ\text{C}$ 800 ^①	A
I_D	Continue Drain Current	$T_C=25^\circ\text{C}$ 220 ^② $T_C=100^\circ\text{C}$ 170	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 400 $T_C=100^\circ\text{C}$ 230	W
$R_{\theta JC}$	Thermal Resistance -Junction to Case	0.45	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	
Drain-Source Avalanche Ratings			
E_{AS}	Avalanche Energy ,Single Pulsed	1400	mJ

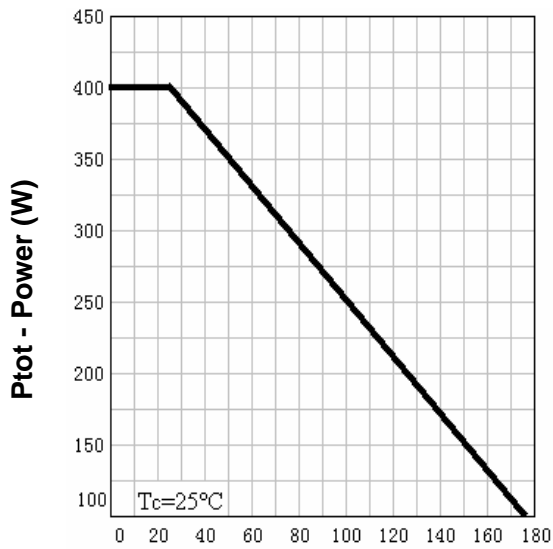
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

	Parameter	Test Condition	RU40220R			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=-250\mu A$	40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$ $T_J=85^{\circ}\text{C}$			1	μA
					30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(3)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=75A$		2.3	3	m Ω
Diode Characteristics						
$V_{SD}^{(3)}$	Diode Forward Voltage	$I_{SD}=75A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=40A, dI_{SD}/dt=100A/\mu s$		74		ns
q_{rr}	Reverse Recovery Charge			148		nC
Dynamic Characteristics ⁽⁴⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.4		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz		5750		pF
C_{oss}	Output Capacitance			1400		
C_{rss}	Reverse Transfer Capacitance			480		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=35V, R_L=35\Omega,$ $I_{DS}=1A, V_{GEN}=10V,$ $R_G=6\Omega$		21		ns
t_r	Turn-on Rise Time			37		
$t_{d(OFF)}$	Turn-off Delay Time			75		
t_f	Turn-off Fall Time			115		
Gate Charge Characteristics ⁽⁴⁾						
Q_g	Total Gate Charge	$V_{DS}=30V, V_{GS}=10V,$ $I_{DS}=40A$		154	218	nC
Q_{gs}	Gate-Source Charge			44		
Q_{gd}	Gate-Drain Charge			47		

- Notes: ① Pulse width limited by safe operating area.
 ② Current limited by package (Limitation Current is 75A)
 ③ Pulse test ; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 ④ Guaranteed by design, not subject to production testing.

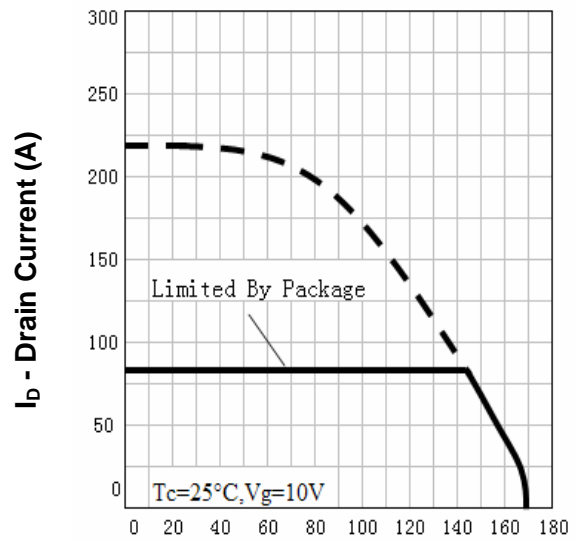
Typical Characteristics

Power Dissipation



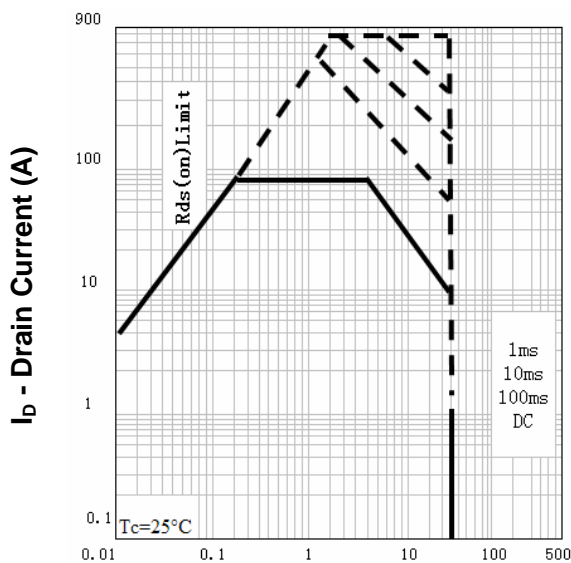
T_j - Junction Temperature (°C)

Drain Current



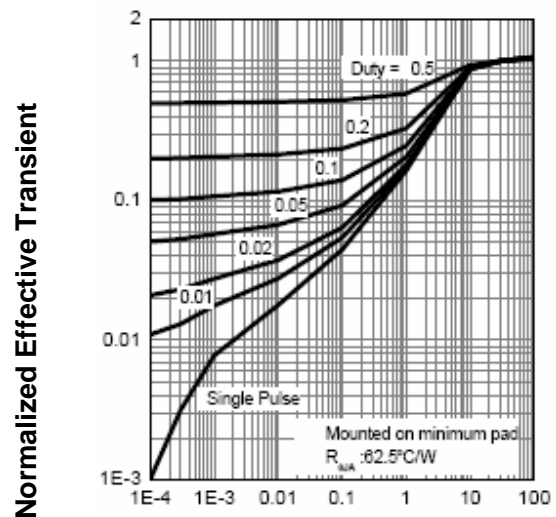
T_j - Junction Temperature (°C)

Safe Operation Area



V_{DS} - Drain-Source Voltage (V)

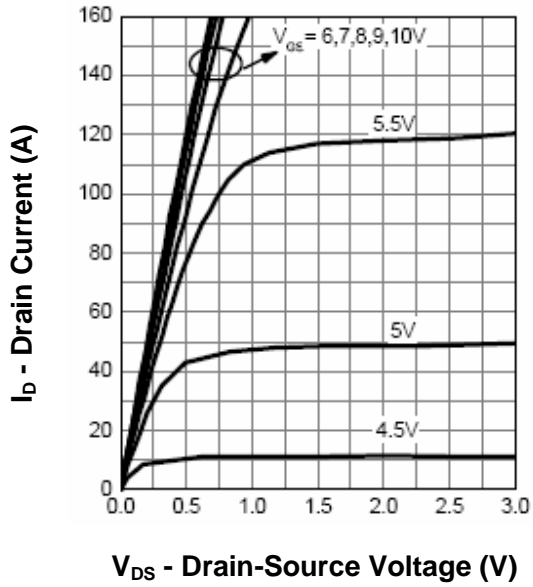
Thermal Transient Impedance



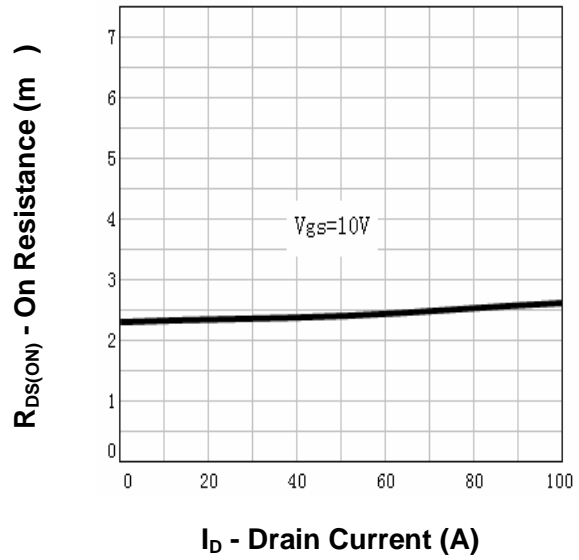
Square Wave Pulse Duration (sec)

Typical Characteristics

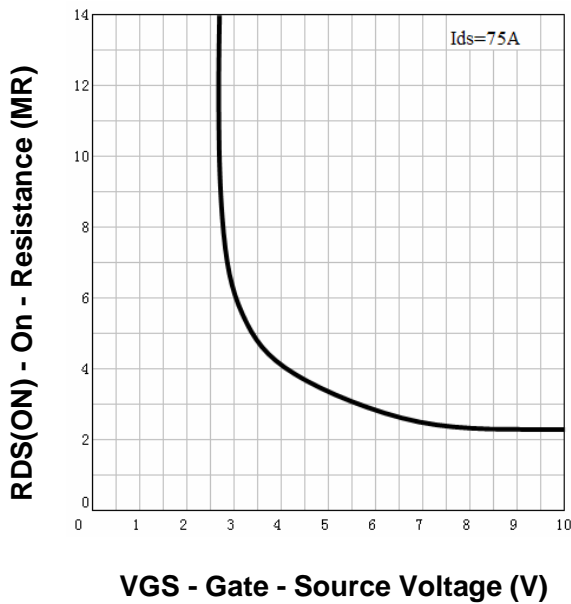
Output Characteristics



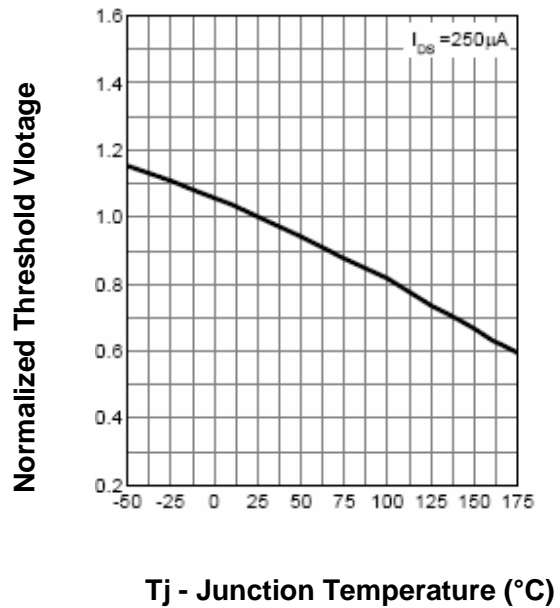
Drain-Source On Resistance



Drain-Source On Resistance

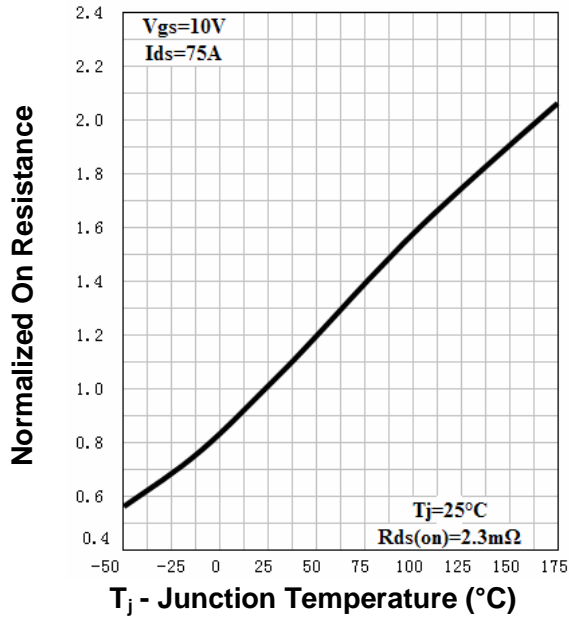


Gate Threshold Voltage

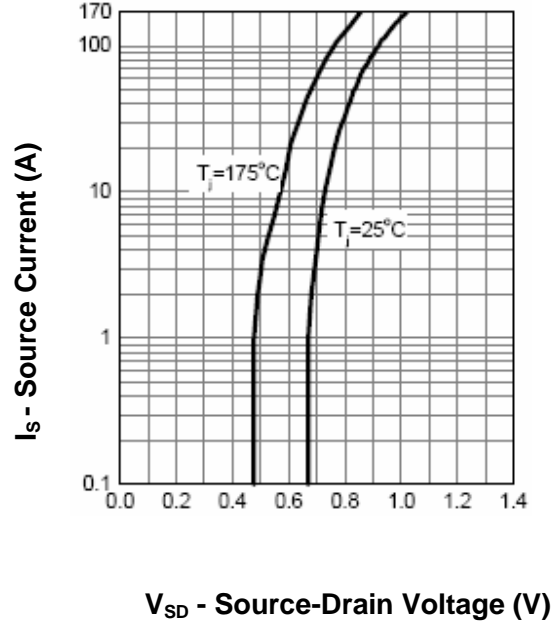


Typical Characteristics

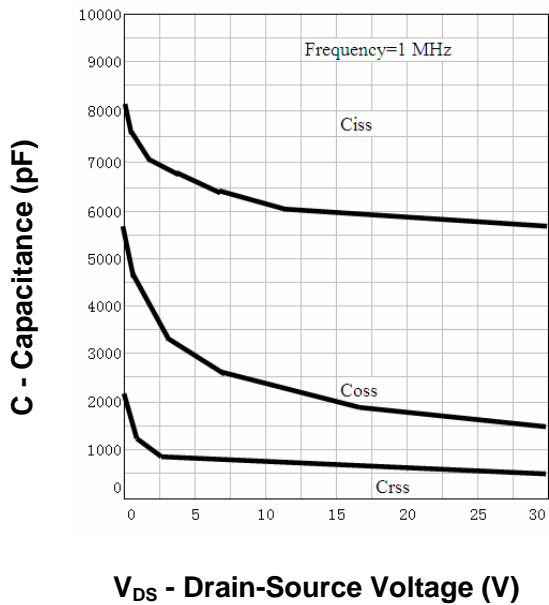
Drain-Source On Resistance



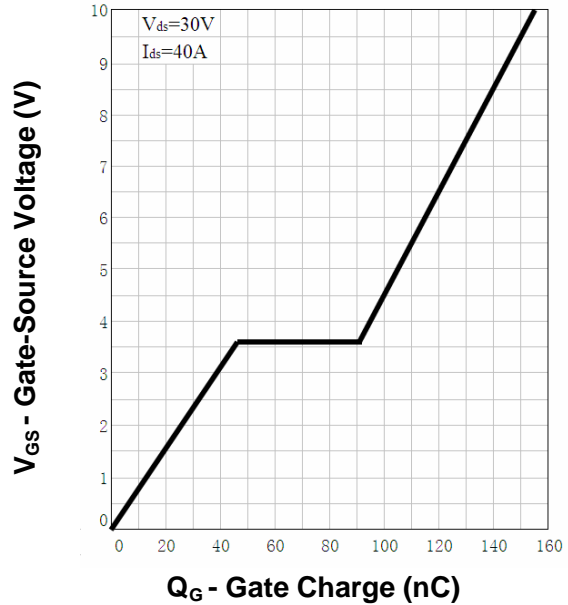
Source-Drain Diode Forward



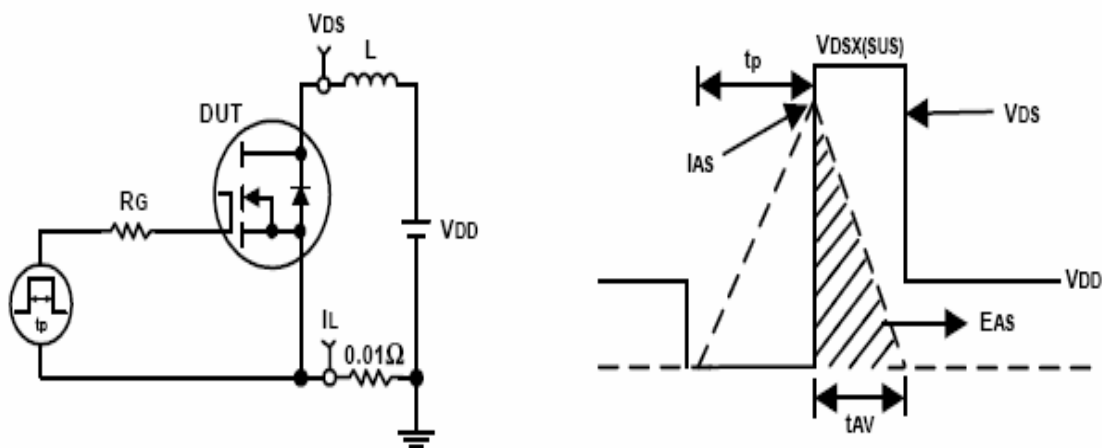
Capacitance



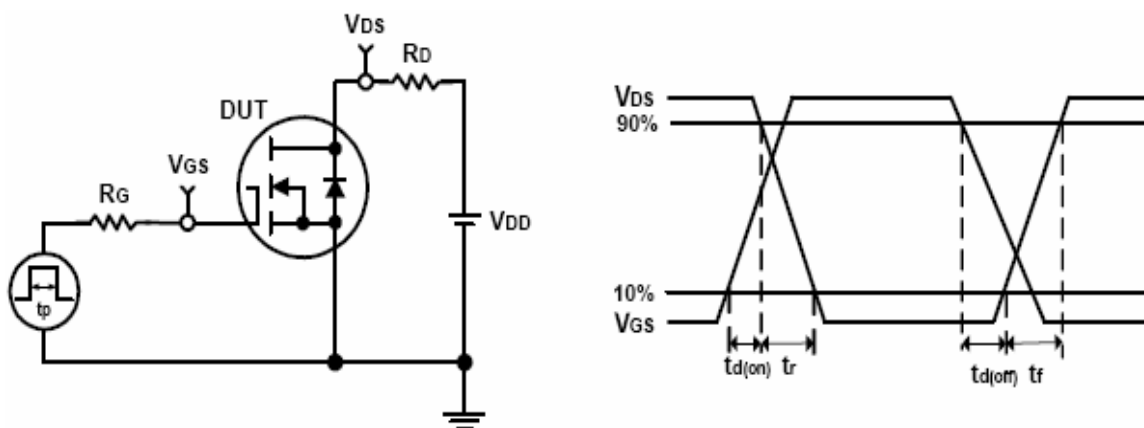
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Ordering and Marking Information**RU40220****Package (Available)**

R: TO-220 ;

Operating Temperature Range

C : -55 to 175 °C

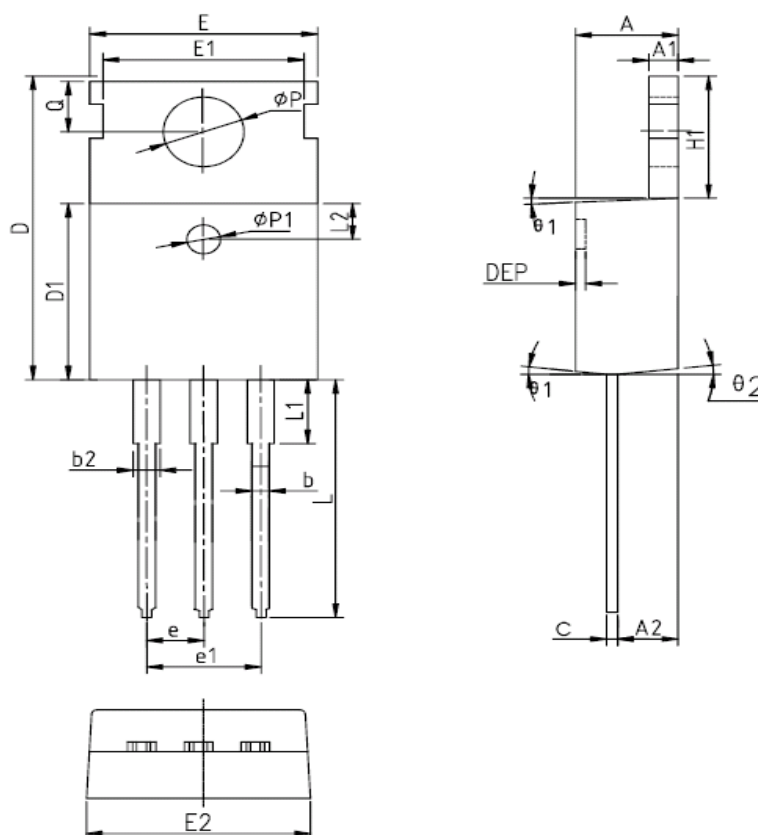
Assembly Material

G : Green & Lead Free Device

Packaging

T : TUBE

TR : Tape & Reel

Package Information
TO-220FB-3L


SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	$\phi p1$	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.27	1.30	1.33	0.050	0.051	0.052	e	2.54BSC			0.1BSC		
A2	2.35	2.40	2.50	0.093	0.094	0.098	e1	5.08BSC			0.2BSC		
b	0.77	-	0.90	0.030	-	0.035	H1	6.40	6.50	6.60	0.252	0.256	0.260
b2	1.23	-	1.36	0.048	-	0.054	L	12.75	-	13.17	0.502	-	0.519
C	0.48	0.50	0.52	0.019	0.020	0.021	L1	-	-	3.95	-	-	0.156
D	15.40	15.60	15.80	0.606	0.614	0.622	L2	2.50REF.			0.098REF.		
D1	9.00	9.10	9.20	0.354	0.358	0.362	ϕp	3.57	3.60	3.63	0.141	0.142	0.143
DEP	0.05	0.10	0.20	0.002	0.004	0.008	Q	2.73	2.80	2.87	0.107	0.110	0.113
E	9.70	9.90	10.10	0.382	0.389	0.398	$\theta 1$	5°	7°	9°	5°	7°	9°
E1	-	8.70	-	-	0.343	-	$\theta 2$	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.401							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

Customer Service

Worldwide Sales and Service:

Sales@ruichips.com

Technical Support:

Technical@ruichips.com

Investor Relations Contacts:

Investor@ruichips.com

Marcom Contact:

Marcom@ruichips.com

Editorial Contact:

Editorial@ruichips.com

HR Contact:

HR@ruichips.com

Legal Contact:

Legal@ruichips.com

Shen Zhen RUICHIPS Semiconductor CO., LTD

Room 501, the 5floor An Tong Industrial Building,
NO.207 Mei Hua Road Fu Tian Area Shen Zhen City, CHINA

TEL: (86-755) 8311-5334

FAX: (86-755) 8311-4278

E-mail: Sales-SZ@ruichips.com